

N-Channel Enhancement Mode MOSFET

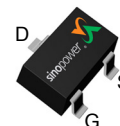
Features

- 20V/6.5A
 - $R_{DS(ON)}=19.8m\Omega(max.)@V_{GS}=10V$
 - $R_{DS(ON)}=24m\Omega(max.)@V_{GS}=4.5V$
 - $R_{DS(ON)}=33m\Omega(max.)@V_{GS}=2.5V$
 - $R_{DS(ON)}=60.8m\Omega(max.)@V_{GS}=1.8V$
- ESD Protection
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

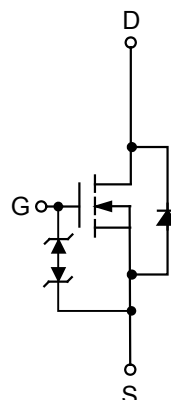
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description



SOT-23N



N-Channel MOSFET

Ordering and Marking Information

SM2420NS -

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±12	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _A =25°C	0.5	A
I _D ^a	Continuous Drain Current	T _A =25°C	6.5	A
		T _A =70°C	5.2	
I _{DM} ^b	Pulsed Drain Current	T _A =25°C	26	
P _D ^a	Maximum Power Dissipation	T _A =25°C	1.25	W
		T _A =70°C	0.8	
R _{θJA} ^a	Thermal Resistance-Junction to Ambient	t ≤ 10s	66	°C/W
		Steady state	100	
I _{AS} ^c	Avalanche Current, Single pulse	L=0.1mH	8.5	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.1mH	3.6	mJ

Note a : Surface mounted on 1in^2 pad area, steady state $t = 999\text{s}$.

Note b : Pulse width limited by max. junction temperature.

Note c : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

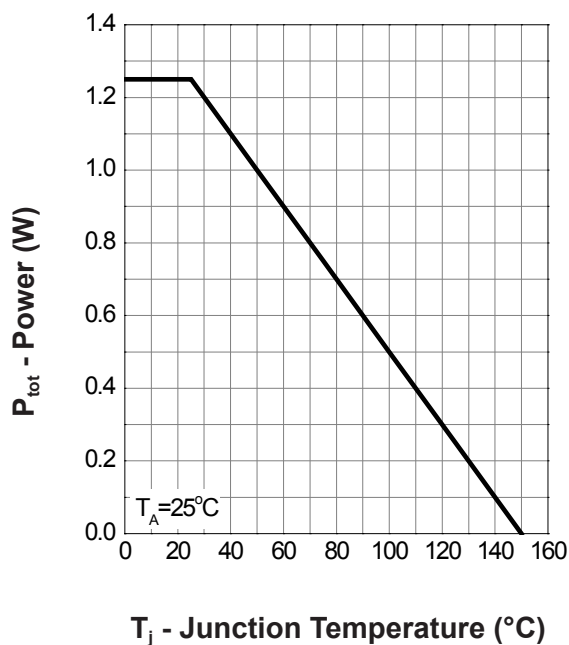
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	0.75	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =6.5A	-	16.5	19.8	mΩ
		V _{GS} =4.5V, I _{DS} =6A	-	18.5	24	
		V _{GS} =2.5V, I _{DS} =5A	-	24.5	33	
		V _{GS} =1.8V, I _{DS} =1A	-	40.5	60.8	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =5A	-	10	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.7	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =6.5A, dI _{SD} /dt=100A/μs	-	6.5	-	ns
t _a	Charge Time		-	3.8	-	
t _b	Discharge Time		-	2.9	-	
Q _{rr}	Reverse Recovery Charge		-	1.8	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2	4	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz	-	460	598	pF
C _{oss}	Output Capacitance		-	86	-	
C _{rss}	Reverse Transfer Capacitance		-	75	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	8.4	16	ns
t _r	Turn-on Rise Time		-	14.6	27	
t _{d(OFF)}	Turn-off Delay Time		-	24	44	
t _f	Turn-off Fall Time		-	3.6	7	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =10V, I _{DS} =6.5A	-	12.8	17.9	nC
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =6.5A	-	6.3	-	
Q _{gth}	Threshold Gate Charge		-	0.1	-	
Q _{gs}	Gate-Source Charge		-	0.35	-	
Q _{gd}	Gate-Drain Charge		-	2.7	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

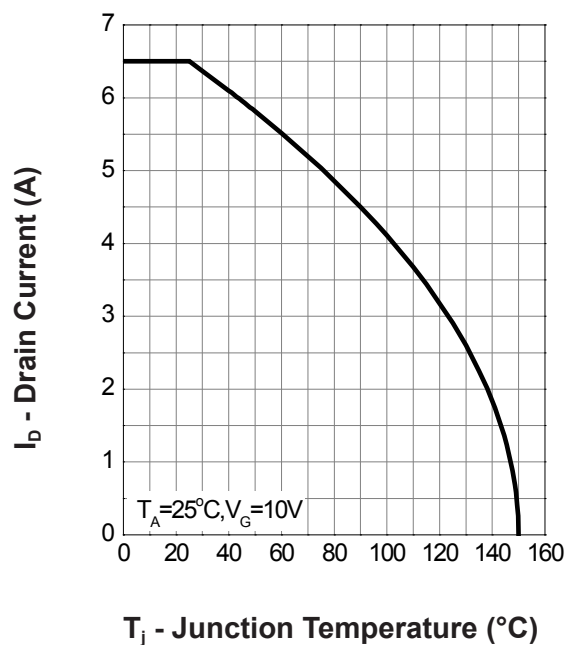
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

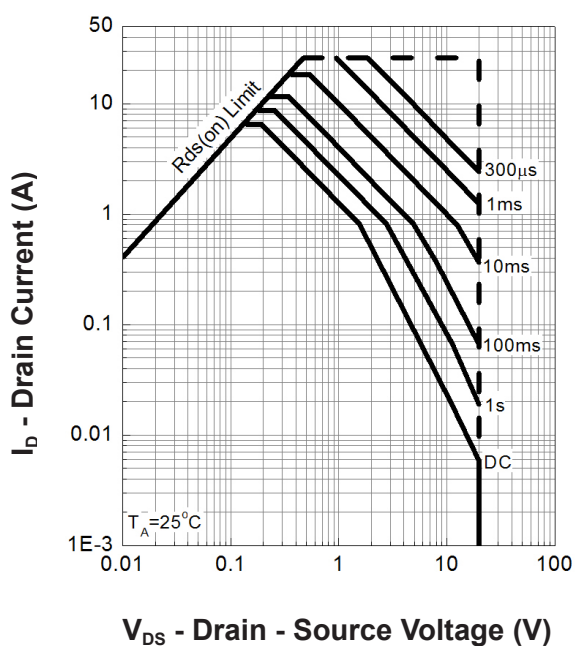
Power Dissipation



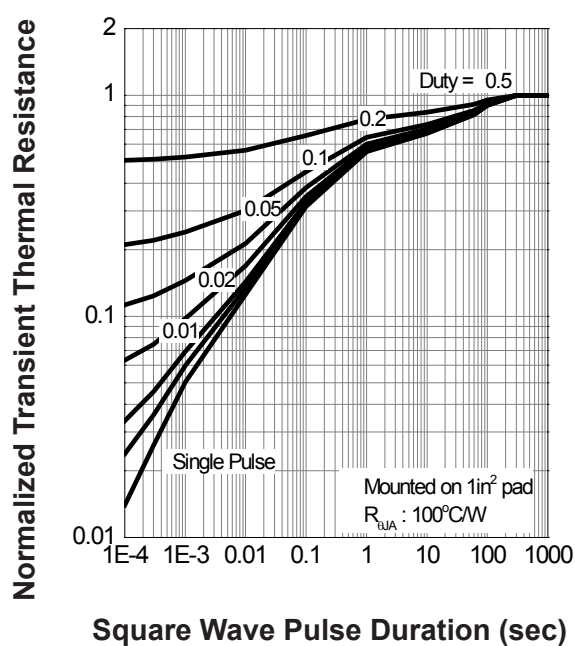
Drain Current



Safe Operation Area

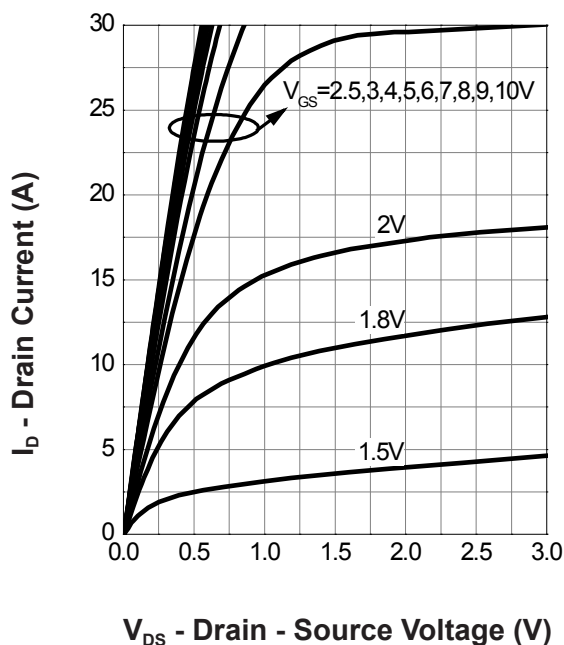


Thermal Transient Impedance

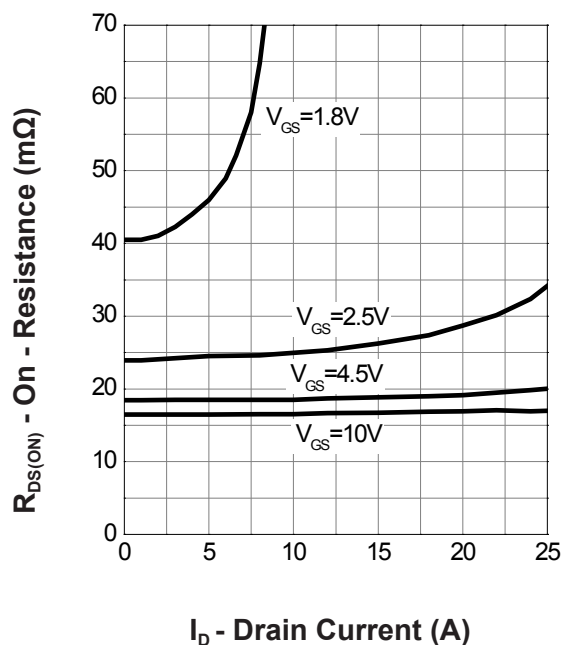


Typical Operating Characteristics(Cont.)

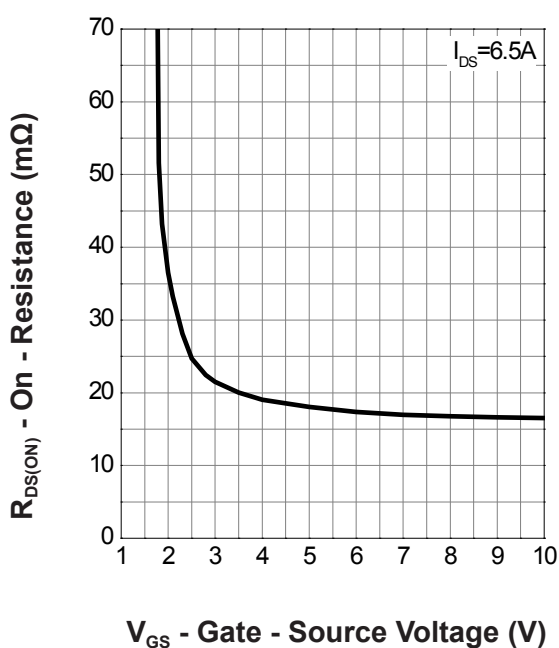
Output Characteristics



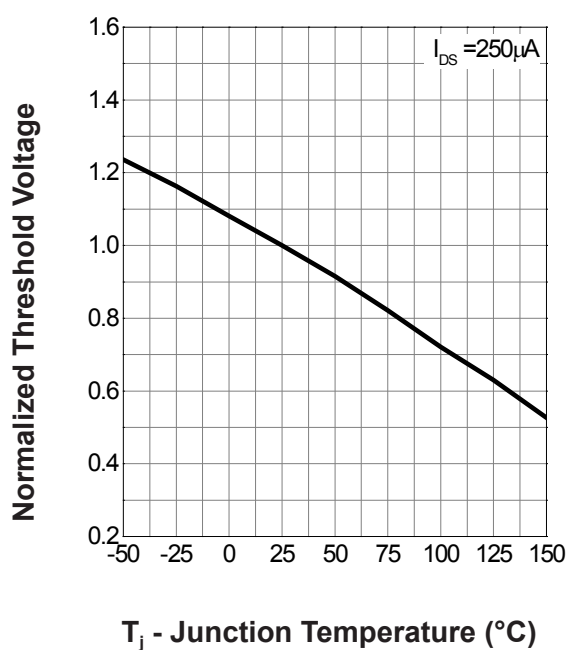
Drain-Source On Resistance



Gate-Source On Resistance

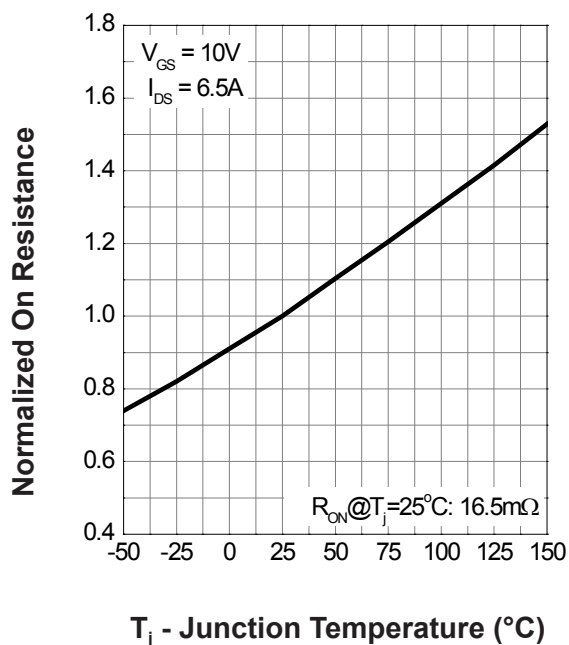


Gate Threshold Voltage

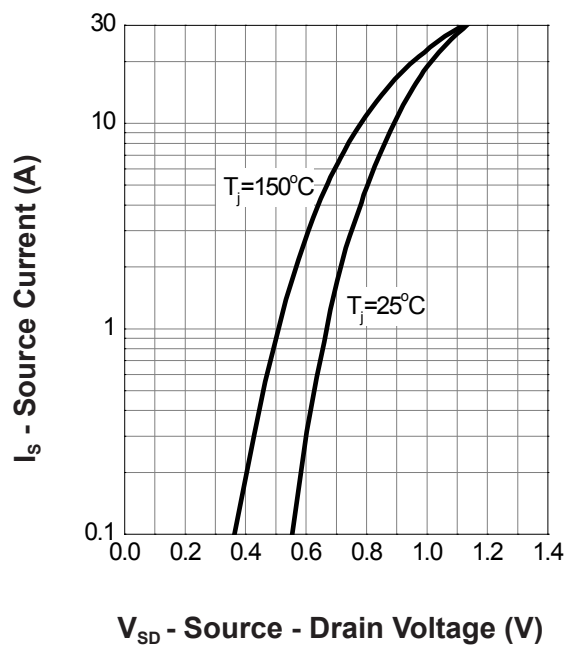


Typical Operating Characteristics(Cont.)

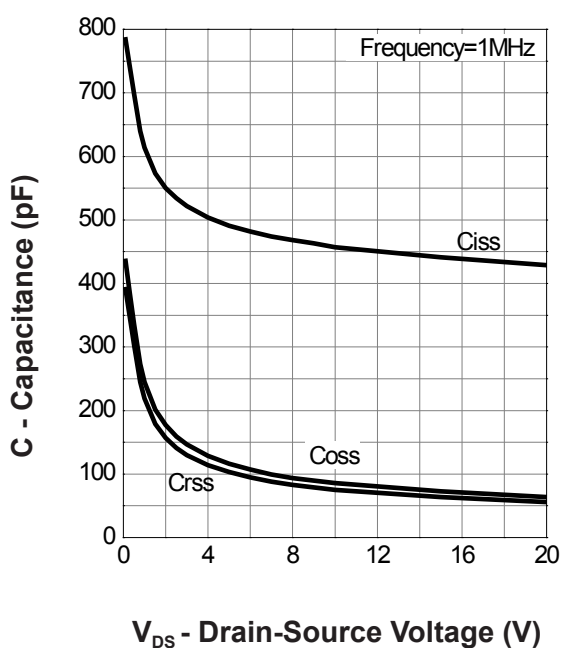
Drain-Source On Resistance



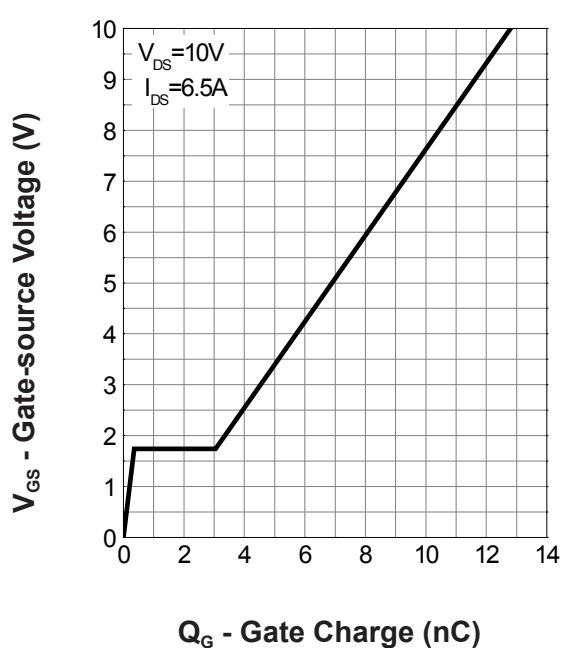
Source-Drain Diode Forward



Capacitance

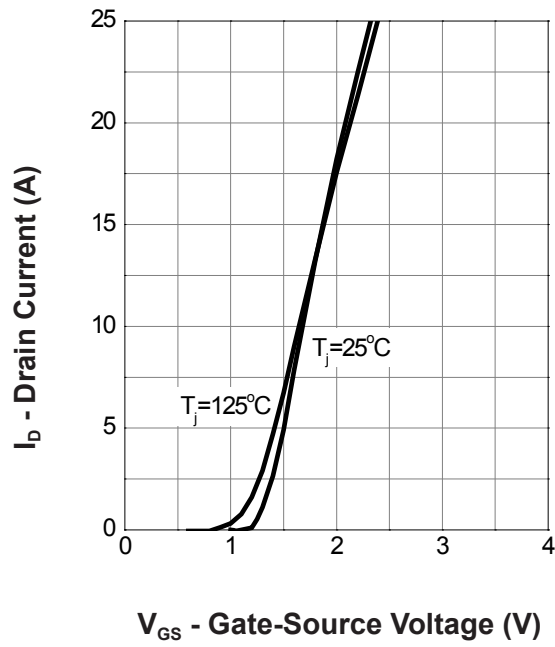


Gate Charge

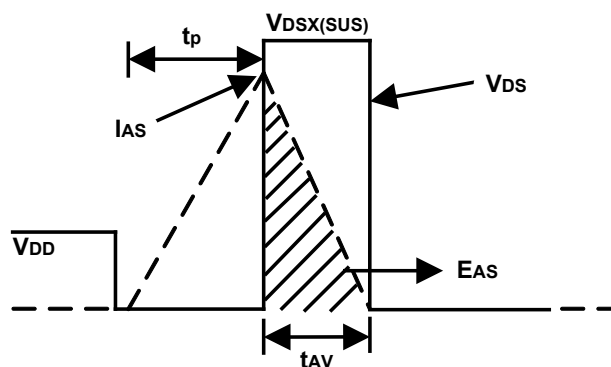
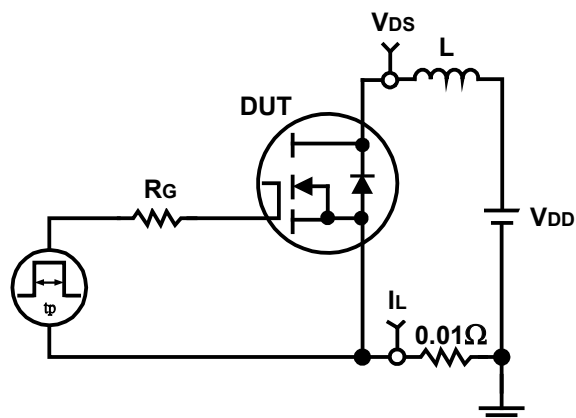


Typical Operating Characteristics(Cont.)

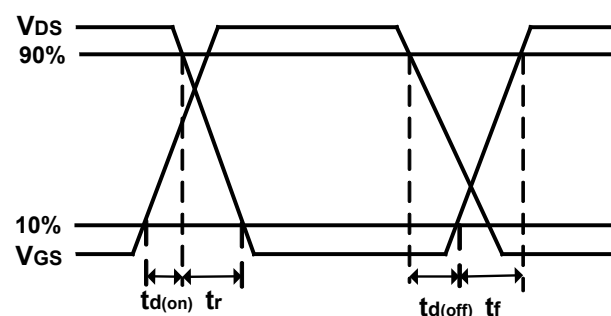
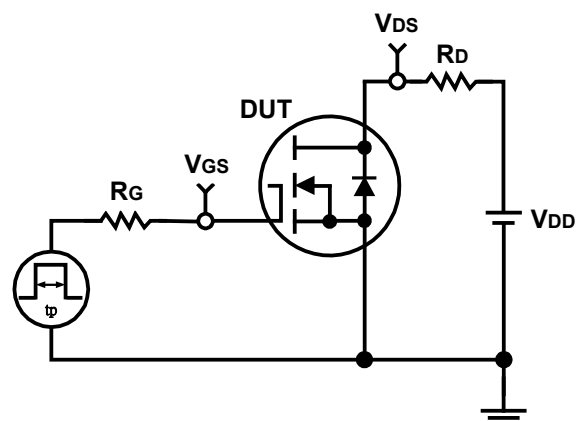
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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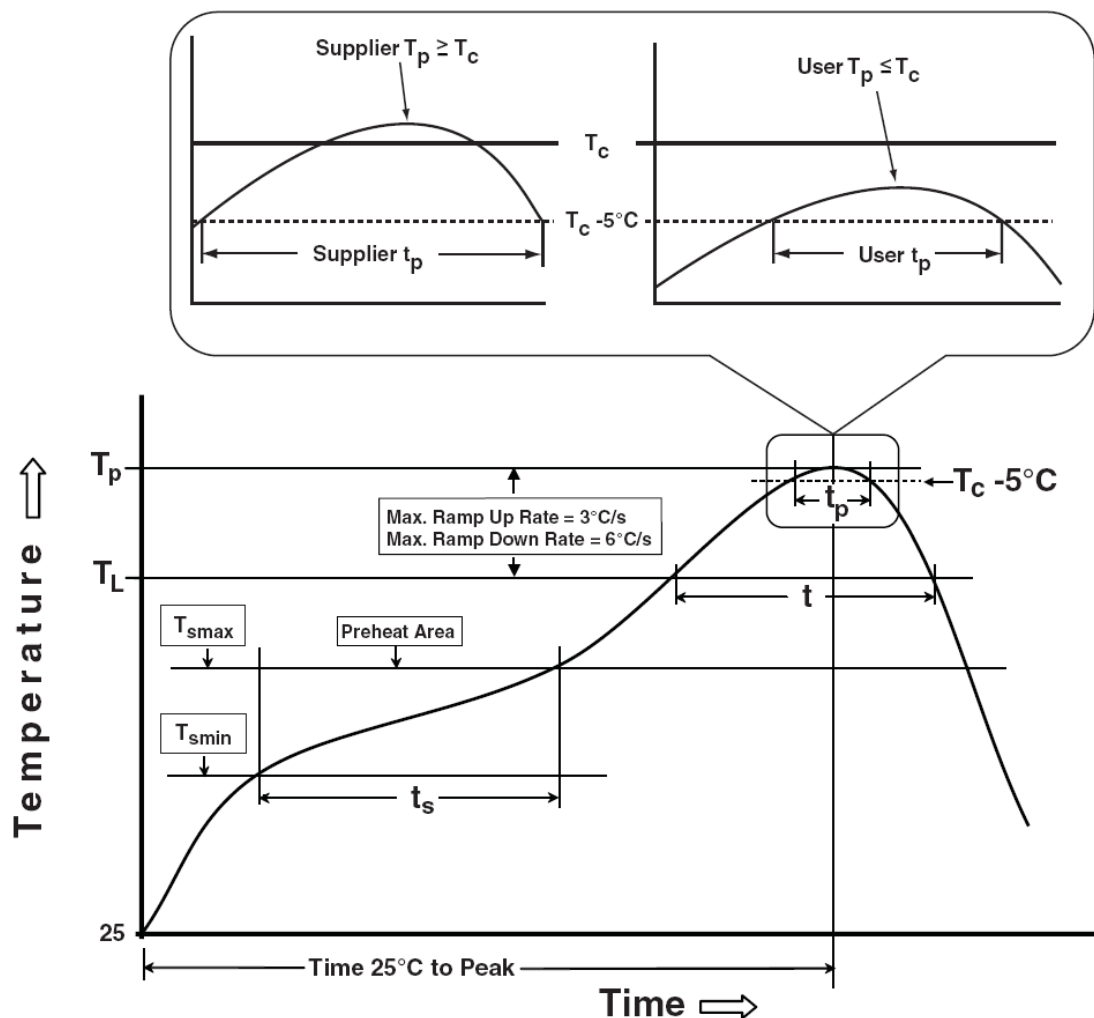
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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